



PATENT APPLICATION

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Applicant: Jae-Yoon SIM and Jei-Hwan YOO

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INFORMATION DISCLOSURE CITATION
FORM PTO-1449 (Modified)U.S. PATENT DOCUMENTS

<u>Exam</u> <u>Init</u>	<u>Ref</u>	<u>Document</u> <u>Number</u>	<u>Issue</u> <u>Date</u>	<u>Name</u>	<u>Class</u>	<u>Sub-</u> <u>Class</u>
TJC	—	6,097,665	August 1, 2000	Tomishima et al.	—	—
TJC	—	6,147,914	Nov. 14, 2000	Leung et al.	—	—

FOREIGN PATENT DOCUMENTS

	<u>Document</u> <u>Number</u>	<u>Publication</u> <u>Date</u>	<u>Country</u>	<u>Name</u>
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OTHER DOCUMENTS

<u>Exam</u> <u>Init</u>	<u>Ref</u>	<u>(Including Author, Title, Date, Pertinent Pages, etc.)</u>
TJC	—	1998 Symposium on VLSI Circuits Digest of Technical Papers P94-95 "A precise On-chip voltage Generator for a Giga-Scale DRAM with a Negative Word-line Scheme"
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Examiner: T. CunninghamDate Considered: 2/13/02RECEIVED
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